

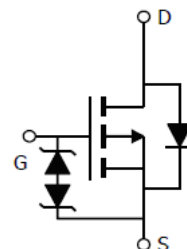
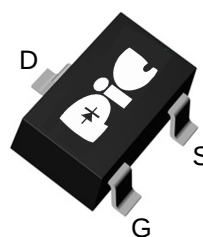
➤ General Description

This PAP3033EB P-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{ds(On)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- ESD Protected
- Low Battery Voltage Operation
- SOT-523 package design

➤ SOT-523



➤ Application

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Smart Phones, Pagers

➤ Absolute Maximum Ratings

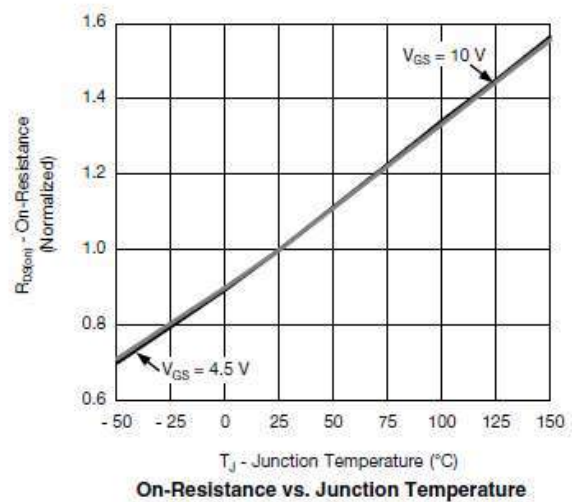
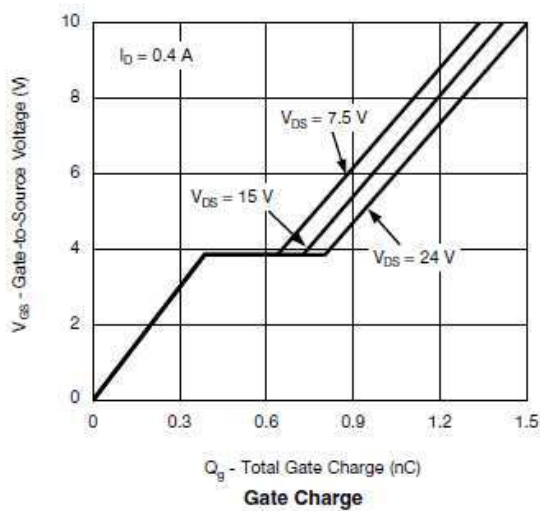
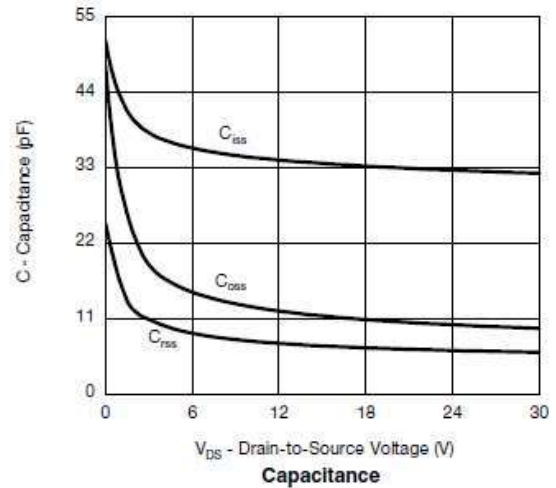
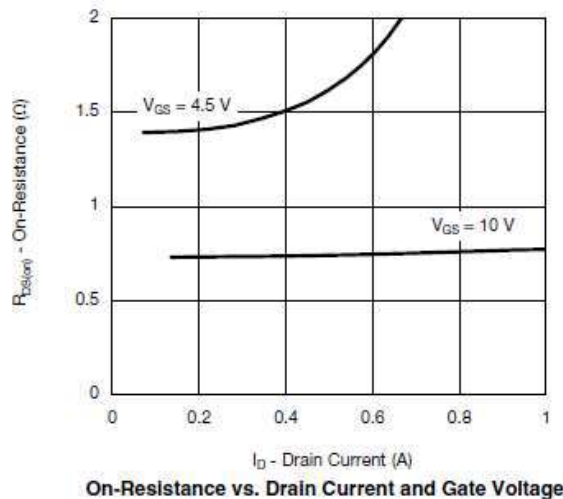
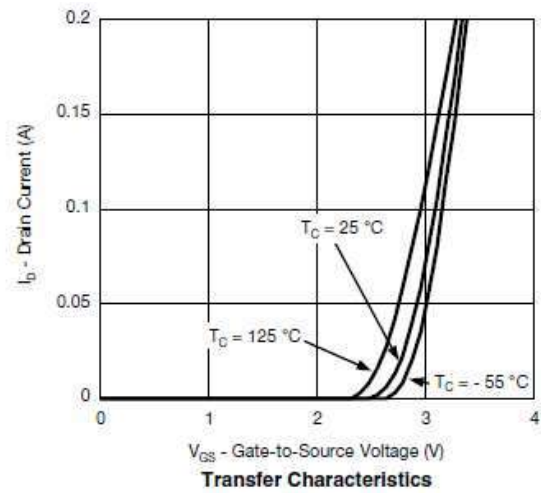
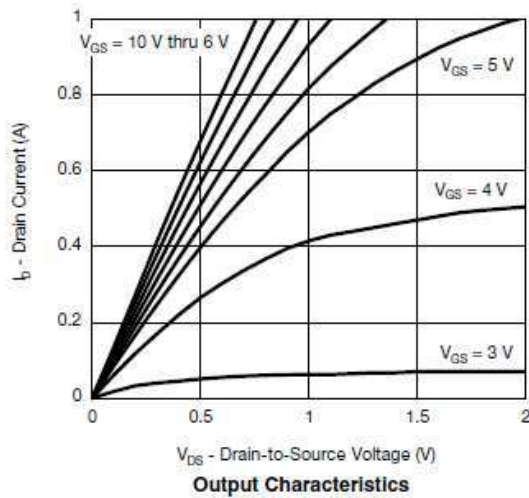
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-30	V
Gate –Source Voltage	V_{GSS}	± 12	V
Continuous Drain Current($T_J=150^\circ C$)	I_D	$T_A=25^\circ C$ -0.6	A
		$T_A=70^\circ C$ -0.2	
Pulsed Drain Current	I_{DM}	-1.0	A
Continuous Source Current(Diode Conduction)	I_S	-0.3	A
Power Dissipation	P_D	$T_A=25^\circ C$ 0.27	W
		$T_A=70^\circ C$ 0.16	
Operating Junction Temperature	T_J	-55/150	$^\circ C$
Storage Temperature Range	T_{STG}	-55/150	$^\circ C$

➤ Electrical Characteristics ($T_A=25^\circ C$ Unless otherwise noted)

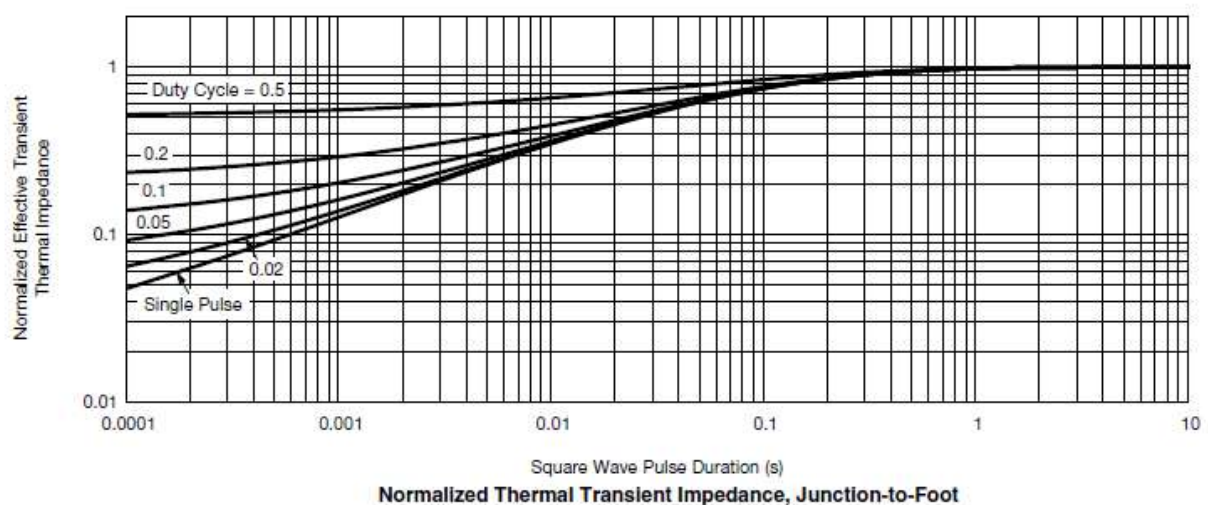
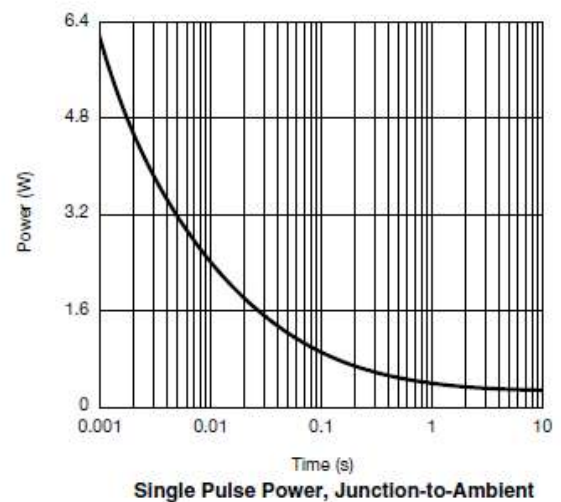
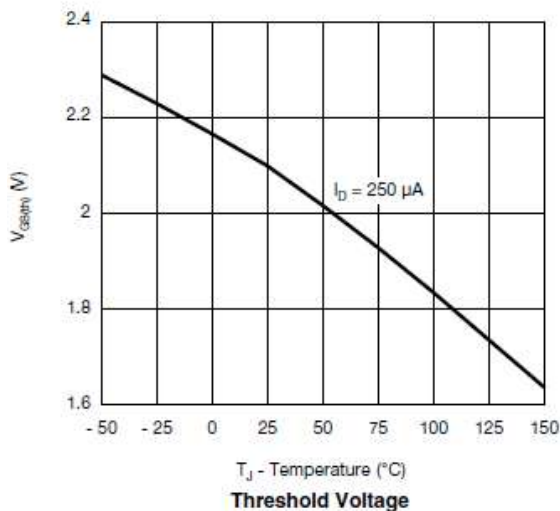
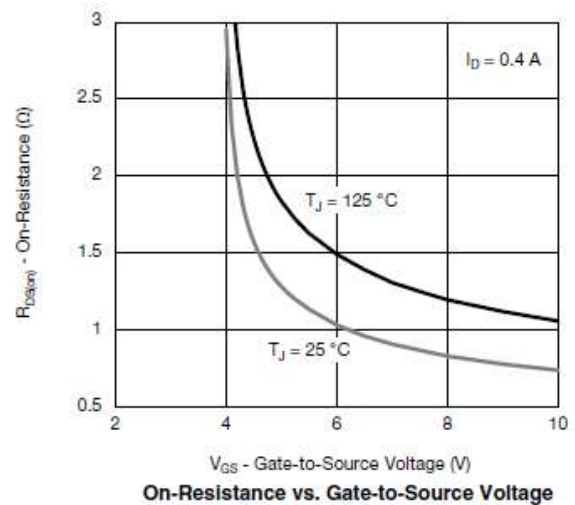
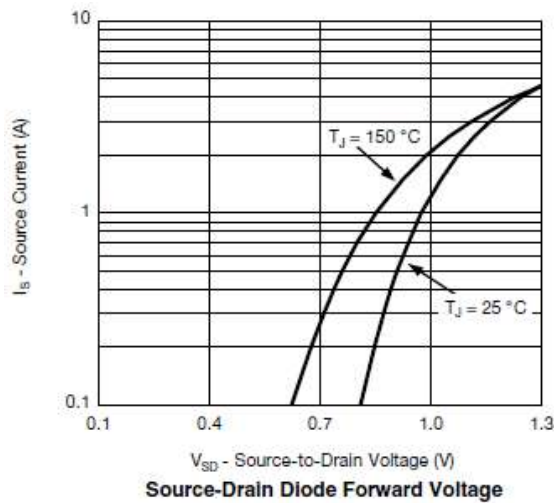
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.7		-1.5	V
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			± 5	mA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$			-1	uA
		$V_{DS}=-24V, V_{GS}=0V$ $T_J=85^\circ C$			-5	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 5V, V_{GS}=4.5V$	0.5			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-0.6A$		560	900	m Ω
		$V_{GS}=-4.5V, I_D=-0.3A$		730	1150	
		$V_{GS}=-2.5V, I_D=-0.2A$		1000	1450	
Forward Transconductance	g_{FS}	$V_{DS}=-15V, I_D=-0.5A$		1		S
Diode Forward Voltage	V_{SD}	$I_S=-0.3A, V_{GS}=0V$		0.65	1.2	V
Dynamic						
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V$ $f=1MHz$		34		pF
Output Capacitance	C_{oss}			12		
Reverse Transfer Capacitance	C_{rss}			8		
Total Gate Charge	Q_g	$V_{DS}=-15V, V_{GS}=-4.5V$ $I_D=-0.4A$		0.8	1.3	nC
Gate-Source Charge	Q_{gs}			0.4		
Gate-Drain Charge	Q_{gd}			0.4		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-15V, R_L=38\Omega$ $I_D=-0.2A, V_{GEN}=-4.5V$ $R_G=1\Omega$		35	50	ns
	t_r			20	30	
Turn-Off Time	$t_{d(off)}$			10	20	
	t_f			10	20	

P-Ch -30V Fast Switching MOSFET
 $V_{DS}=-30V$, $I_D=-0.6A$, $R_{DS(ON)}=900m\Omega$

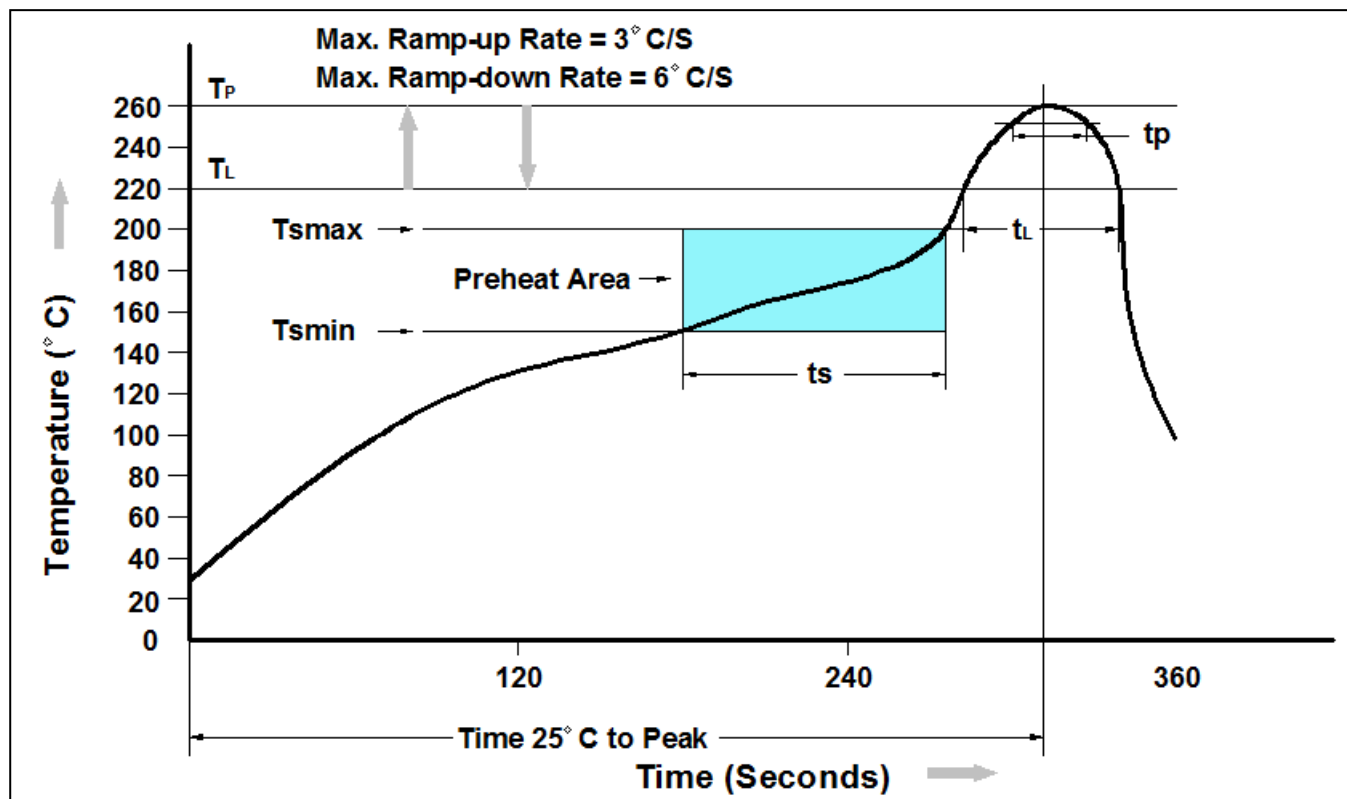
➤ Typical Characteristics



P-Ch -30V Fast Switching MOSFET
 $V_{DS}=-30V$, $I_D=-0.6A$, $R_{DS(on)}=900m\Omega$



➤ Recommand IR Reflow Soldering Thermal Profile

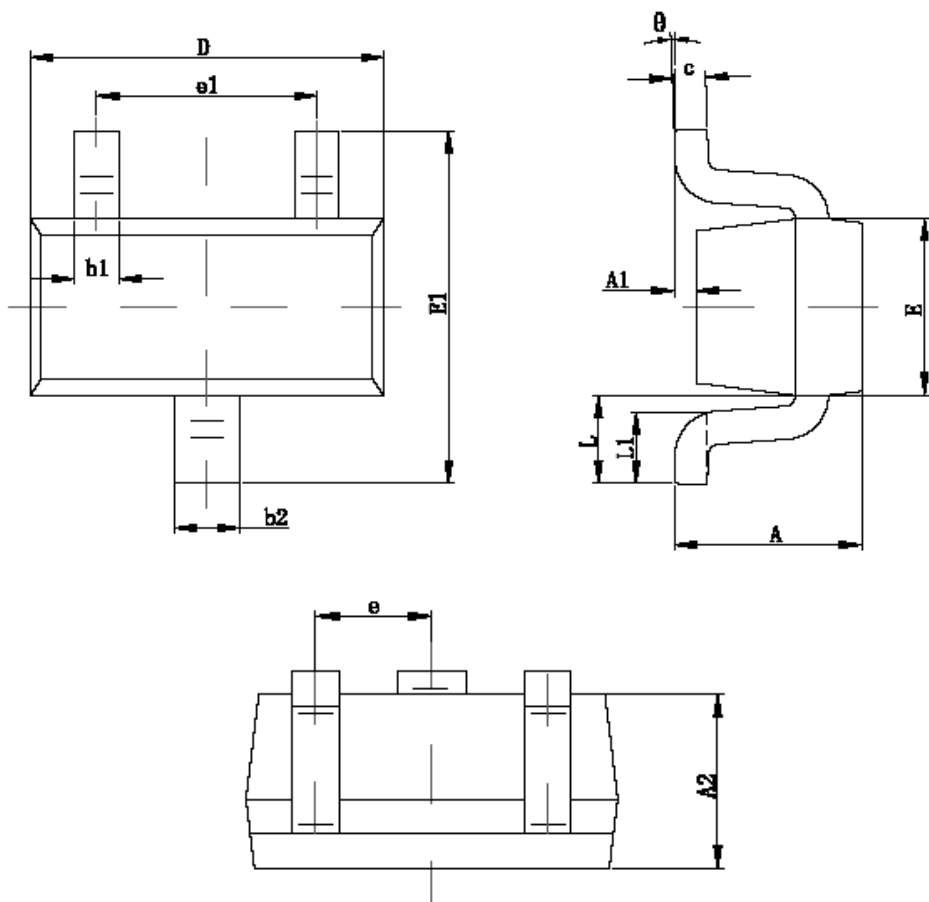


Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmín)	150°C
Temperature Max. (Tsmáx)	200°C
Time (ts) from (Tsmín to Tsmáx)	60-120 seconds
Average Ramp-up Rate (tL to tP)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (tP) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAP3033EB	SOT-523 Reel	3000 pcs

➤ Package Information (SOT-523)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.325	0.010	0.013
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.750	0.850	0.030	0.033
E1	1.450	1.750	0.057	0.069
e	0.500 TYP		0.020 TYP	
e1	0.900	1.100	0.035	0.043
L	0.550 REF		0.022 REF	
L1	0.280	0.440	0.011	0.017
θ	0°	4°	0°	4°

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